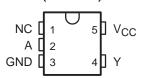
- EPIC[™] (Enhanced-Performance Implanted CMOS) Process
- Operating Range 2-V to 5.5-V V_{CC}
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages

DBV OR DCK PACKAGE (TOP VIEW)



NC - No internal connection

description

The SN74AHC1G14 contains one inverter gate. The device performs the Boolean function $Y = \overline{A}$.

The device functions as an independent inverter gate, but because of the Schmitt action, gates may have different input threshold levels for positive- (V_{T+}) and negative-going (V_{T-}) signals.

The SN74AHC1G14 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

INPUT A	OUTPUT Y
Н	L
L	Н

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	–0.5 V to 7 V
Input voltage range, V _I (see Note 1)	–0.5 V to 7 V
Output voltage range, VO (see Note 1)	0.5 V to V _{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)	
Output clamp current, I _{OK} (V _O < 0 or V _O > V _{CC})	±20 mA
Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$	±25 mA
Continuous current through V _{CC} or GND	±50 mA
Package thermal impedance, θ_{JA} (see Note 2): DBV package	347°C/W
DCK package	389°C/W
Storage temperature range, T _{sta}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			MIN	MAX	UNIT
V _{CC} Supply voltage				5.5	V
V _I Input voltage				5.5	V
V _O Output voltage				VCC	V
ІОН	$V_{CC} = 2 \text{ V}$ High-level output current $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	V _{CC} = 2 V		-50	μΑ
			-4	mA	
	$V_{CC} = 5 V \pm 0.5 V$			-8	IIIA
		V _{CC} = 2 V		50	μΑ
IOL	Low-level output current $ V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} $ $ V_{CC} = 5 \text{ V} \pm 0.5 \text{ V} $			4	mA
				8	IIIA
T _A Operating free-air temperature			-40	85	°C



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	Vas	T,	Δ = 25°C	;	MIN	MAX	UNIT
PARAMETER	TEST CONDITIONS	Vcc	MIN	TYP	MAX			UNIT
V _{T+}		3 V	1.2		2.2	1.2	2.2	
Positive-going		4.5 V	1.75		3.15	1.75	3.15	V
input threshold voltage		5.5 V	2.15		3.85	2.15	3.85	
V _T _		3 V	0.9		1.9	0.9	1.9	
Negative-going		4.5 V	1.35		2.75	1.35	2.75	V
input threshold voltage		5.5 V	1.65		3.35	1.65	3.35	
		3 V	0.3		1.2	0.3	1.2	
ΔV_T Hysteresis ($V_{T+} - V_{T-}$)		4.5 V	0.4		1.4	0.4	1.4	V
11/3/07/07/07/07/07/07/07/07/07/07/07/07/07/		5.5 V	0.5		1.6	0.5	1.6	
		2 V	1.9	2		1.9		V
	ΙΟΗ = -50 μΑ	3 V	2.9	3		2.9		
Voн		4.5 V	4.4	4.5		4.4		
	$I_{OH} = -4 \text{ mA}$	3 V	2.58			2.48		
	$I_{OH} = -8 \text{ mA}$	4.5 V	3.94			3.8		
		2 V			0.1		0.1	
	I _{OL} = 50 μA	3 V			0.1		0.1	V
VOL		4.5 V			0.1		0.1	
	I _{OL} = 4 mA	3 V			0.36		0.44	
	I _{OL} = 8 mA	4.5 V			0.36		0.44	
lį	V _I = V _{CC} or GND	0 V to 5.5 V			±0.1		±1	μΑ
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			1		10	μΑ
C _i	V _I = V _{CC} or GND	5 V		2	10		10	pF

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V \pm 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	то	LOAD	T _A = 25°C			MIN	MAX	UNIT							
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	IVIIIV	IVIAA	UNIT							
tPLH	^	Y	Y	Y	Y	A Y C _L =	0: 45 = 5		8.3	12.8	1	15	20			
t _{PHL}	^						'	1	'	'	'	'	T T	C _L = 15 pF	CL = 15 pr	
tPLH	Δ.	Y	A V C F0.75		10.8	16.3	1	18.5								
t _{PHL}	1 A		$C_L = 50 \text{ pF}$		10.8	16.3	1	18.5	ns							

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

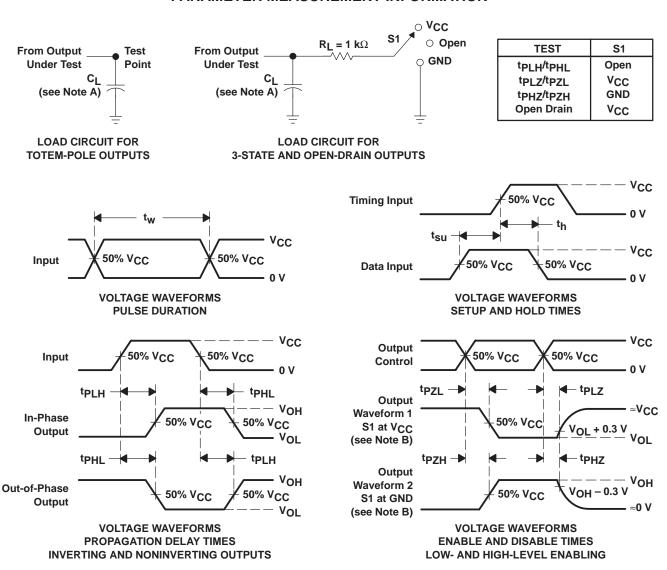
PARAMETER	FROM	то	TO LOAD	T _A = 25°C			MIN	MAX	UNIT						
	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	IVIIIV	IVIAA	ONIT						
^t PLH	Λ.	Y	0 45 -5		5.5	8.6	1	10	no						
^t PHL	A		'	'	'	'	C _L = 15 pF	C[= 15 pr		5.5	8.6	1	10	ns	
t _{PLH}	A	Y	Y	C: _ 50 pF		7	10.6	1	12	no					
t _{PHL}	А			Y	Ť	Y	Y	Y	Y	l Y	C _L = 50 pF		7	10.6	1



operating characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST C	ONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load,	f = 1 MHz	9	pF

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_r \leq 3$ ns. $t_f \leq 3$ ns.
- D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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